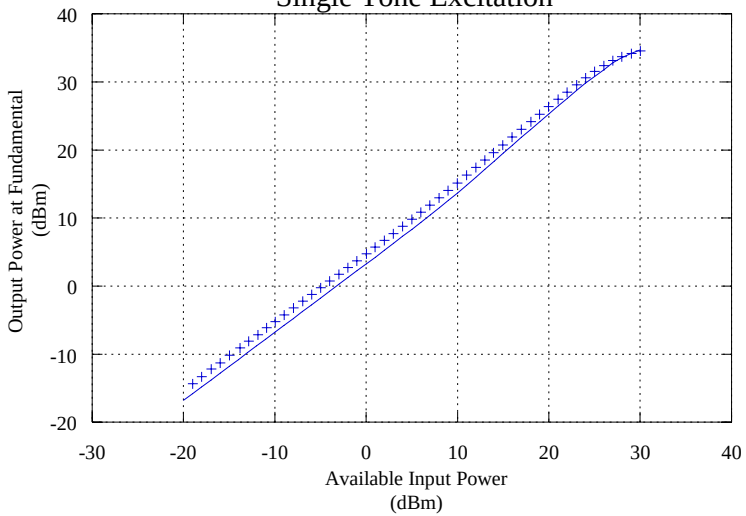
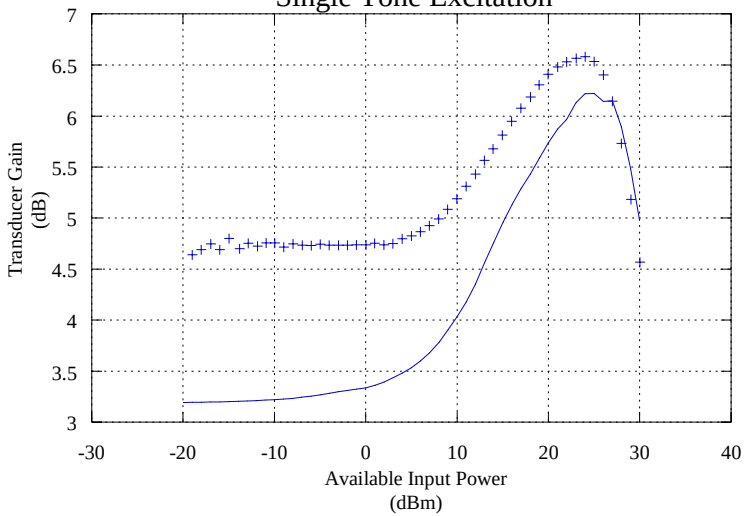
1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
50 ohm Termination
Solid:Simulated & Points:Measured

MOTOROLA

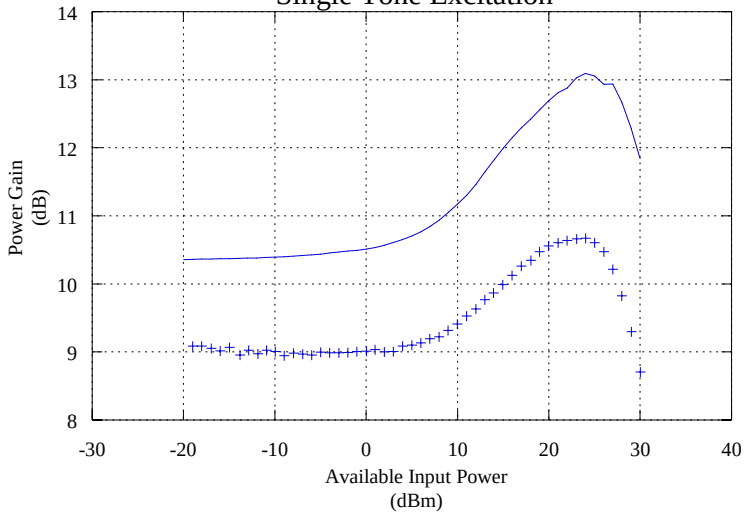
Output Power at Fundamental vs. Available Input Power
Single Tone Excitation



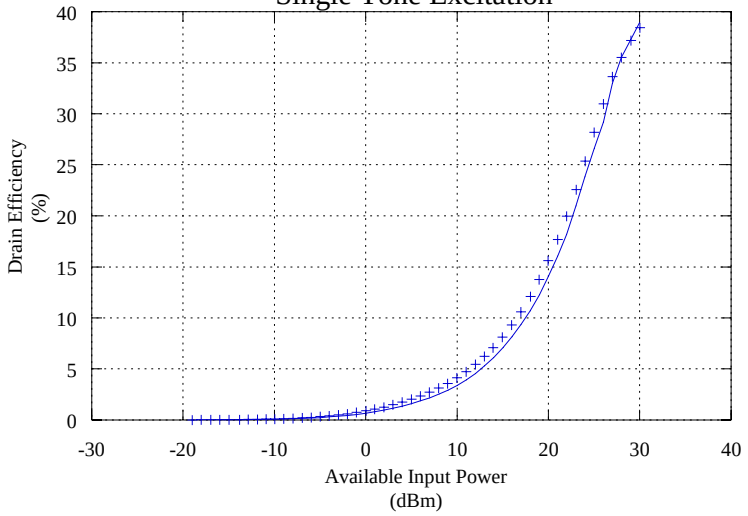
Transducer Gain vs. Available Input Power
Single Tone Excitation



Power Gain vs. Available Input Power
Single Tone Excitation



Drain Efficiency vs. Available Input Power
Single Tone Excitation



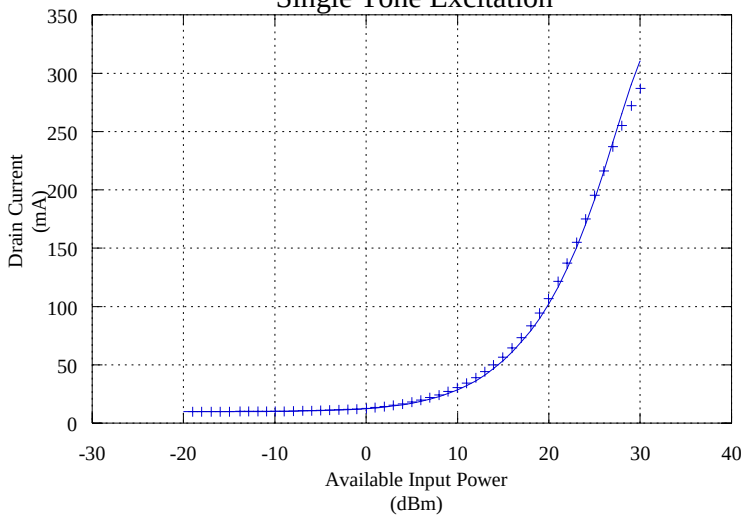
Rev/Date: Rev0/0298

Simulated:hv350d03swp1.txt & Measured:hv350d03.swp

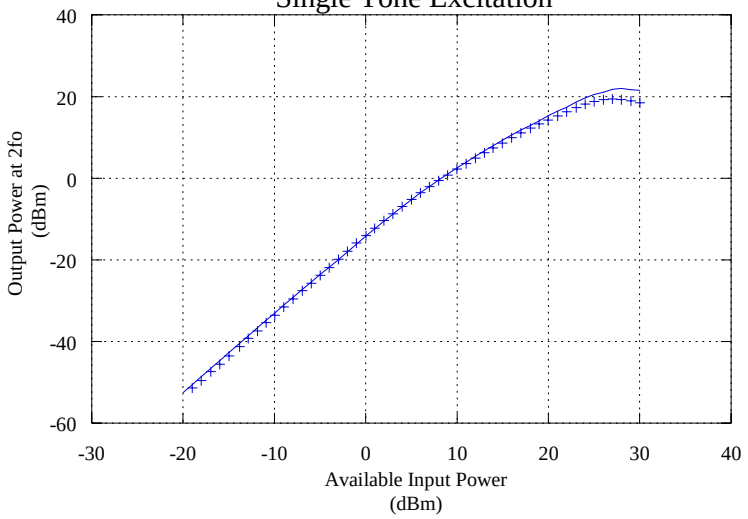
1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
50 ohm Termination
Solid:Simulated & Points:Measured

MOTOROLA

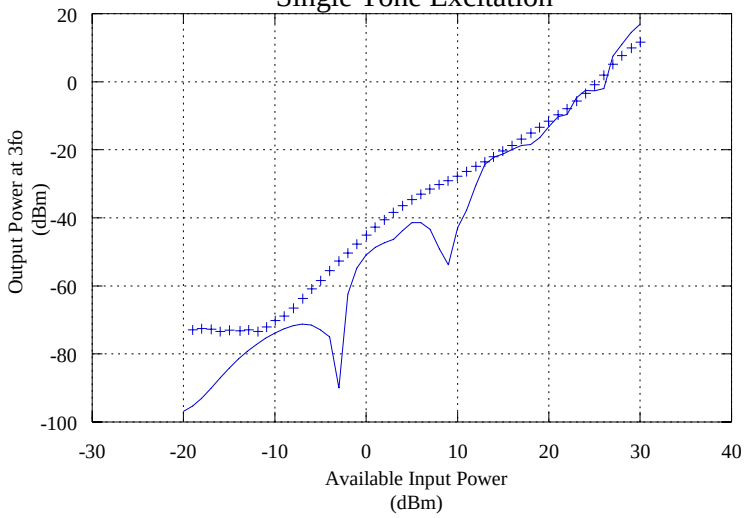
Drain Current vs. Available Input Power
Single Tone Excitation



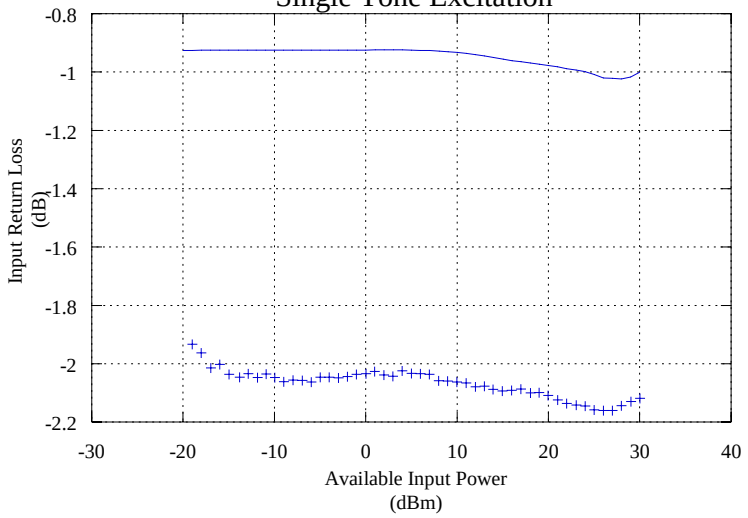
Output Power at 2fo vs. Available Input Power
Single Tone Excitation



Output Power at 3fo vs. Available Input Power
Single Tone Excitation



Input Return Loss vs. Available Input Power
Single Tone Excitation

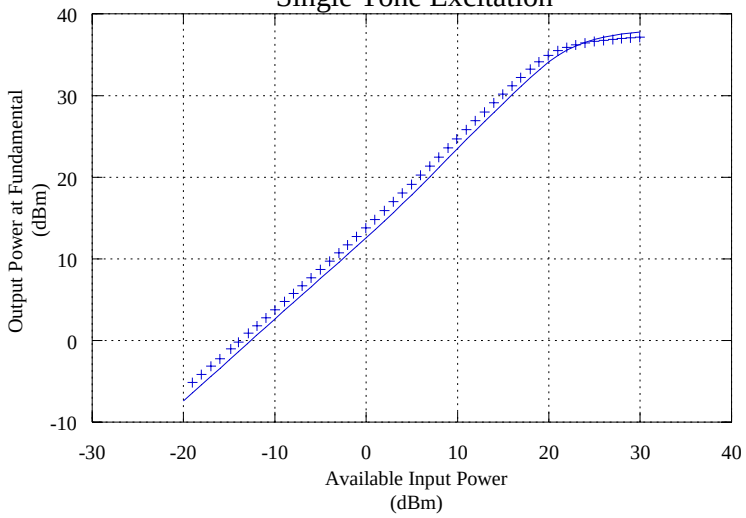


Rev/Date: Rev0/0298

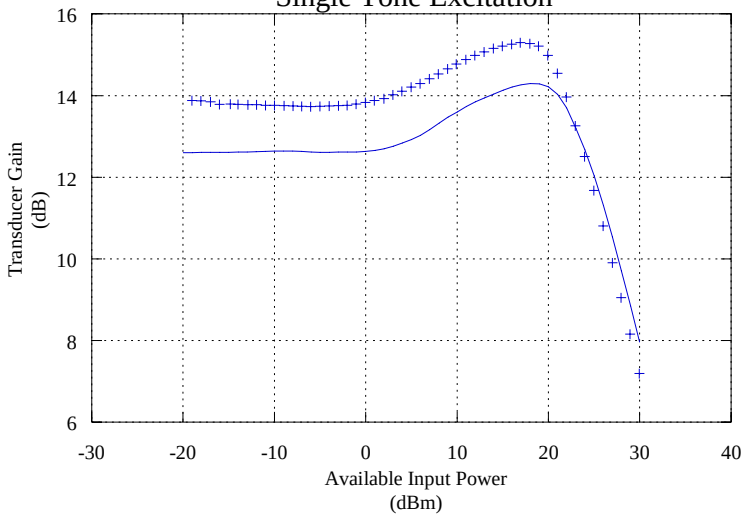
Simulated:hv350d03swp1.txt & Measured:hv350d03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power
Solid:Simulated & Points:Measured

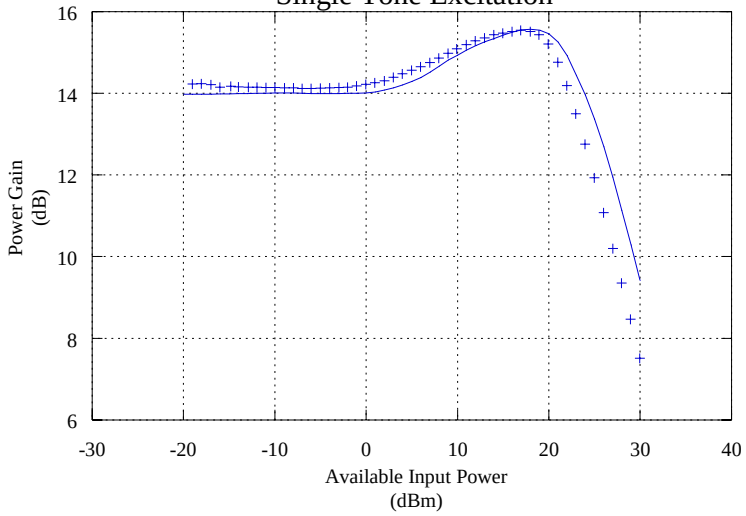
Output Power at Fundamental vs. Available Input Power
Single Tone Excitation



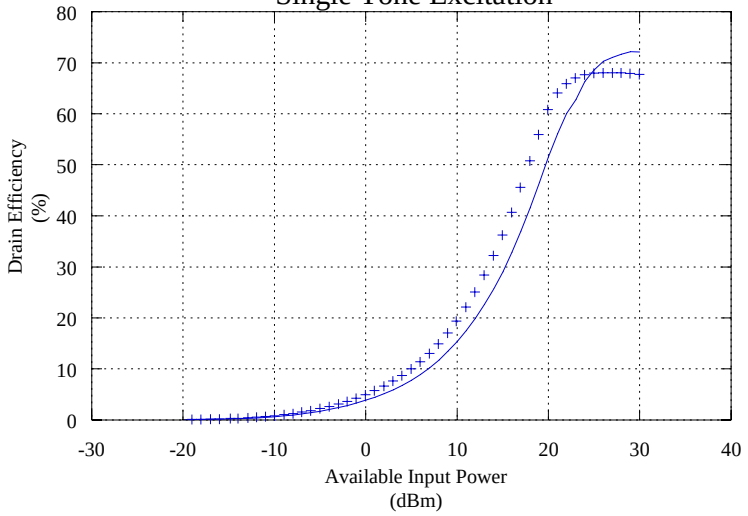
Transducer Gain vs. Available Input Power
Single Tone Excitation



Power Gain vs. Available Input Power
Single Tone Excitation



Drain Efficiency vs. Available Input Power
Single Tone Excitation

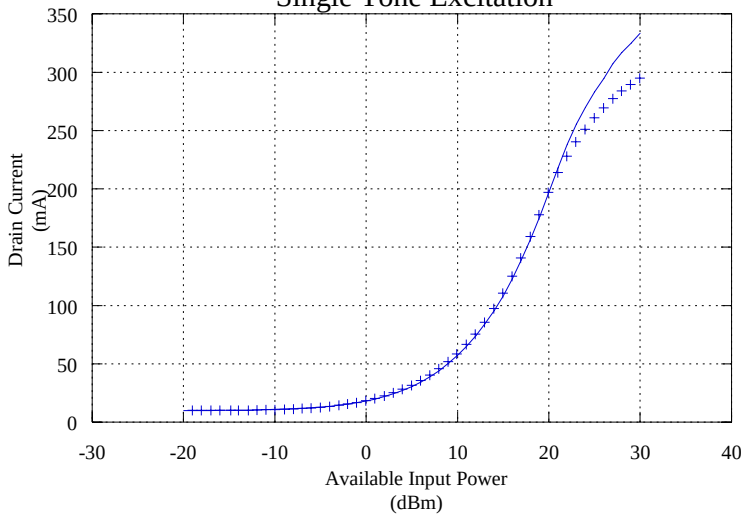


Rev/Date: Rev0/0298

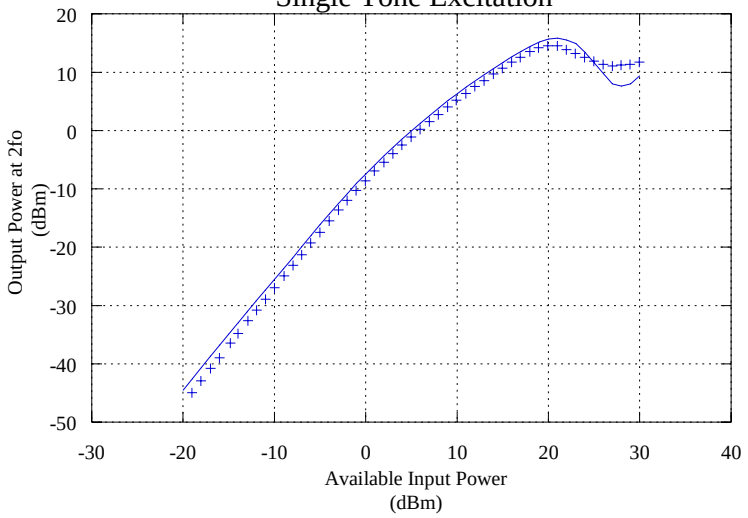
Simulated:hv3pmd03swp1.txt & Measured:hv3pmd03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power
Solid:Simulated & Points:Measured

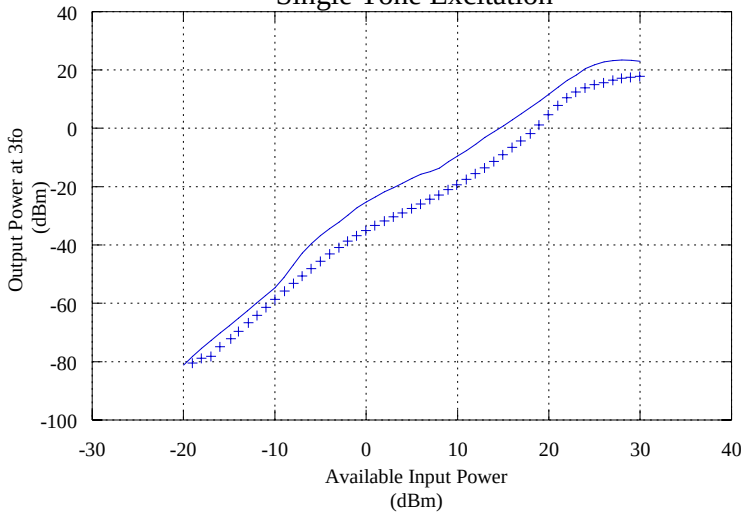
Drain Current vs. Available Input Power
Single Tone Excitation



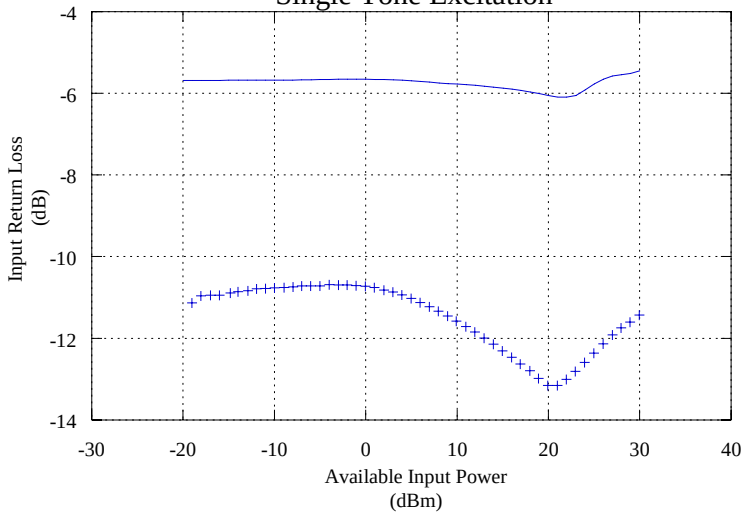
Output Power at 2fo vs. Available Input Power
Single Tone Excitation



Output Power at 3fo vs. Available Input Power
Single Tone Excitation



Input Return Loss vs. Available Input Power
Single Tone Excitation



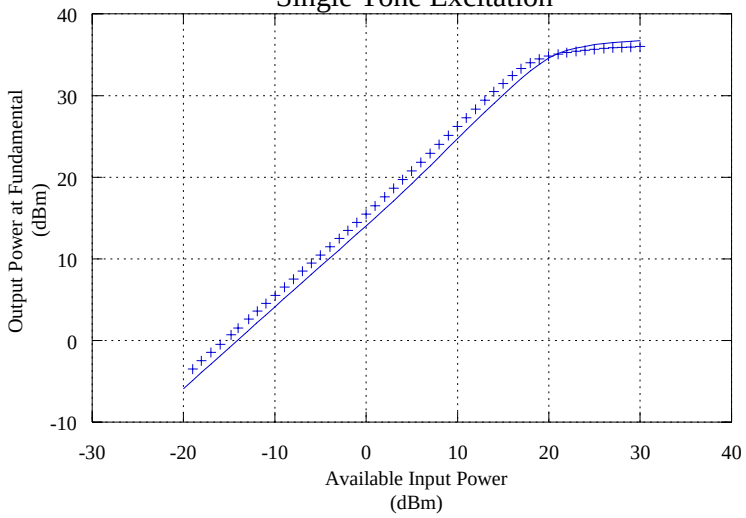
Rev/Date: Rev0/0298

Simulated:hv3pmd03swp1.txt & Measured:hv3pmd03.swp

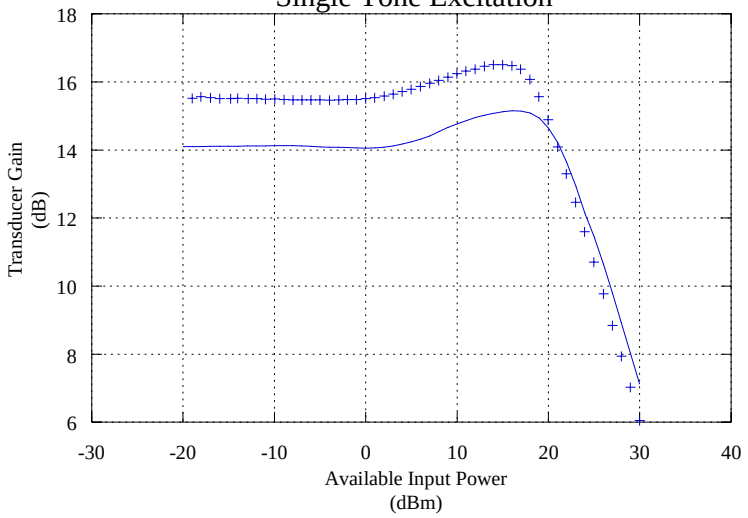
1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Efficiency
Solid:Simulated & Points:Measured

MOTOROLA

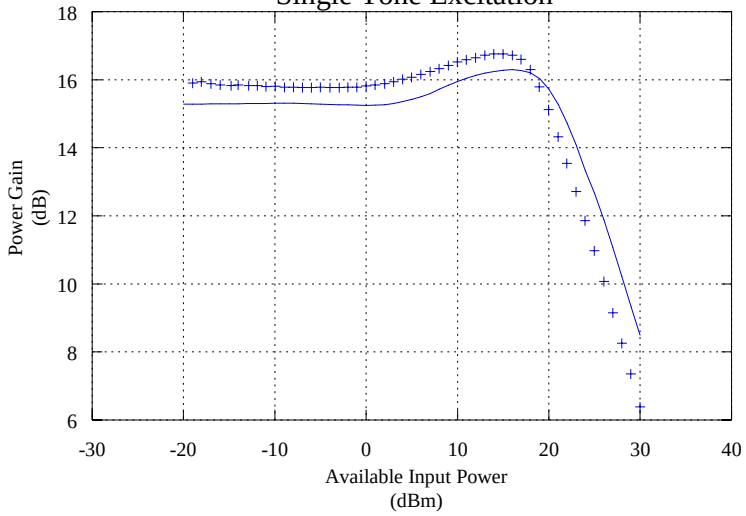
Output Power at Fundamental vs. Available Input Power
Single Tone Excitation



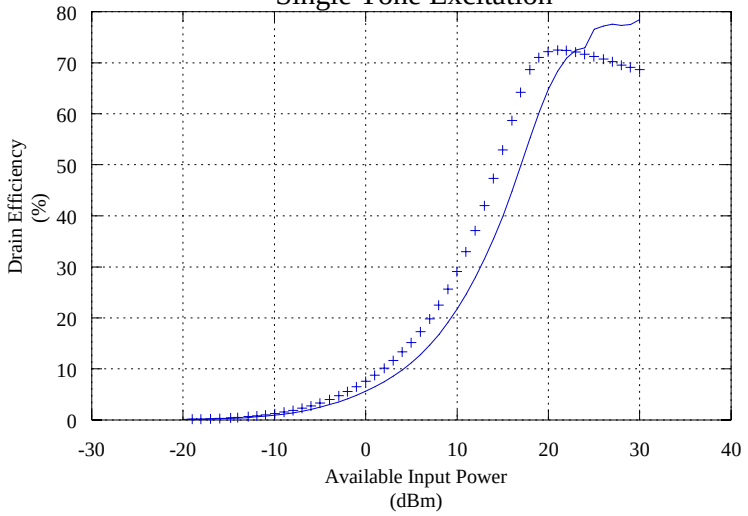
Transducer Gain vs. Available Input Power
Single Tone Excitation



Power Gain vs. Available Input Power
Single Tone Excitation



Drain Efficiency vs. Available Input Power
Single Tone Excitation



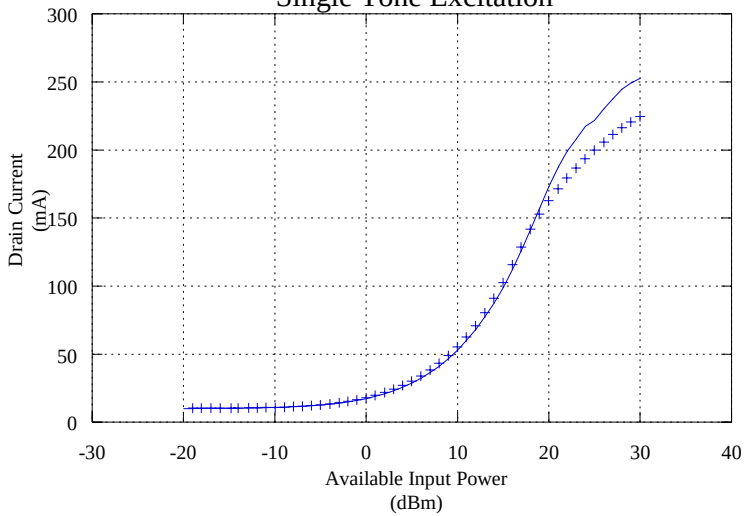
Rev/Date: Rev0/0298

Simulated:hv3emd03swp1.txt & Measured:hv3emd03.swp

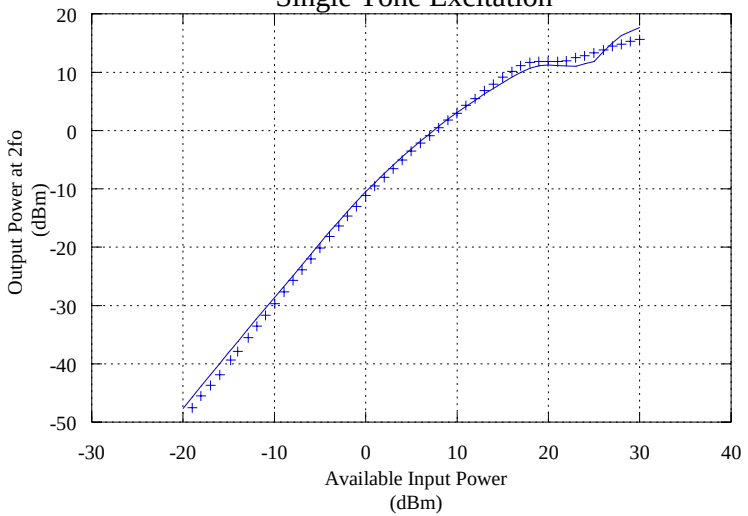
1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Efficiency
Solid:Simulated & Points:Measured

MOTOROLA

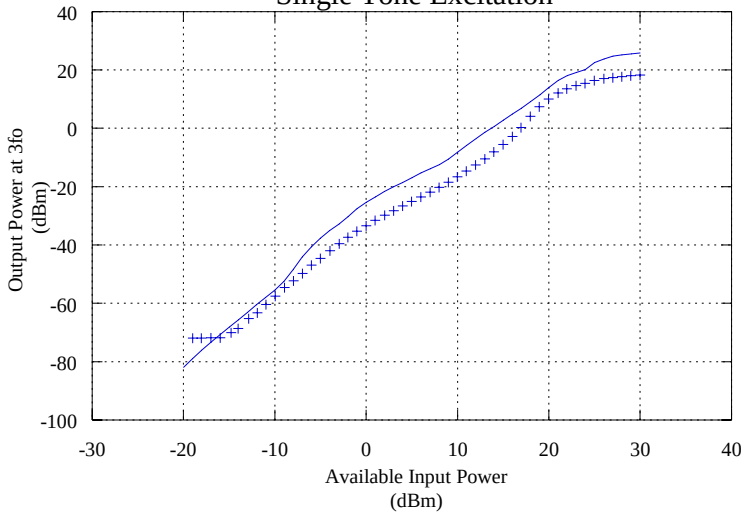
Drain Current vs. Available Input Power
Single Tone Excitation



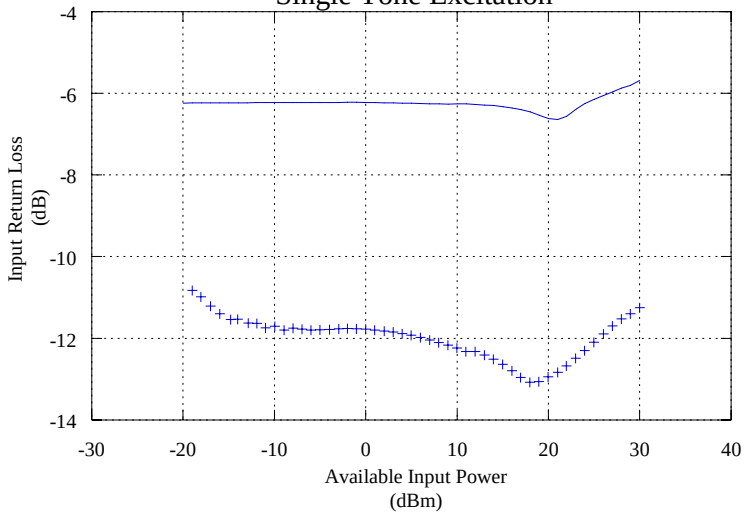
Output Power at 2fo vs. Available Input Power
Single Tone Excitation



Output Power at 3fo vs. Available Input Power
Single Tone Excitation



Input Return Loss vs. Available Input Power
Single Tone Excitation



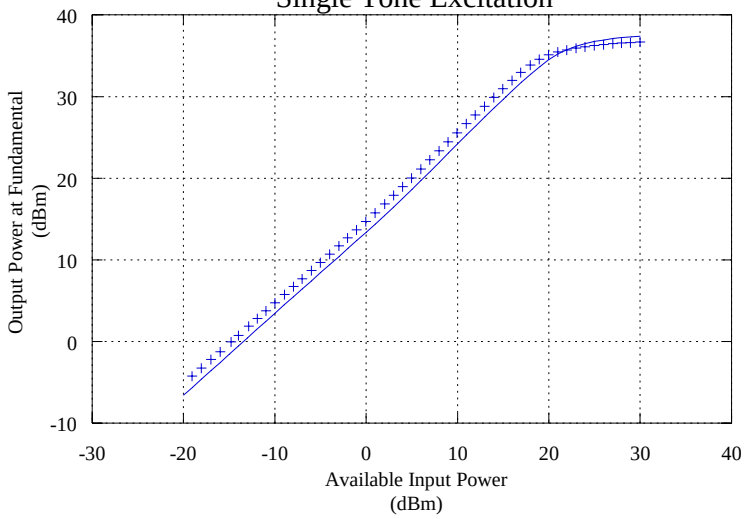
Rev/Date: Rev0/0298

Simulated:hv3emd03swp1.txt & Measured:hv3emd03.swp

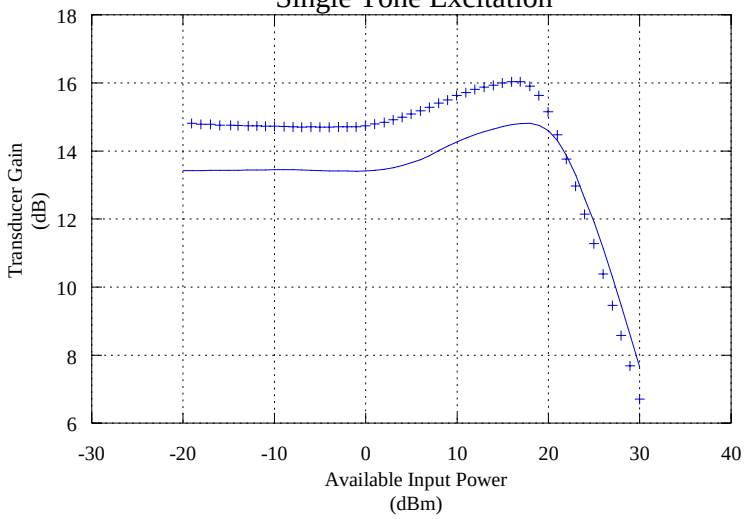
1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power & Efficiency
Solid:Simulated & Points:Measured

MOTOROLA

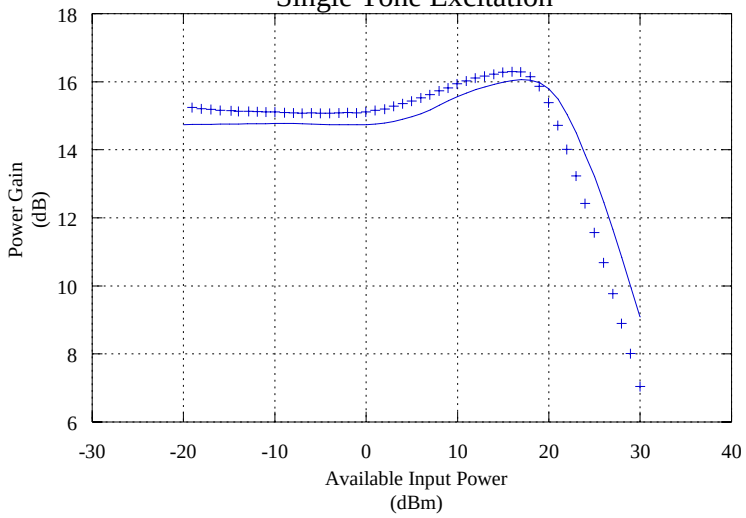
Output Power at Fundamental vs. Available Input Power
Single Tone Excitation



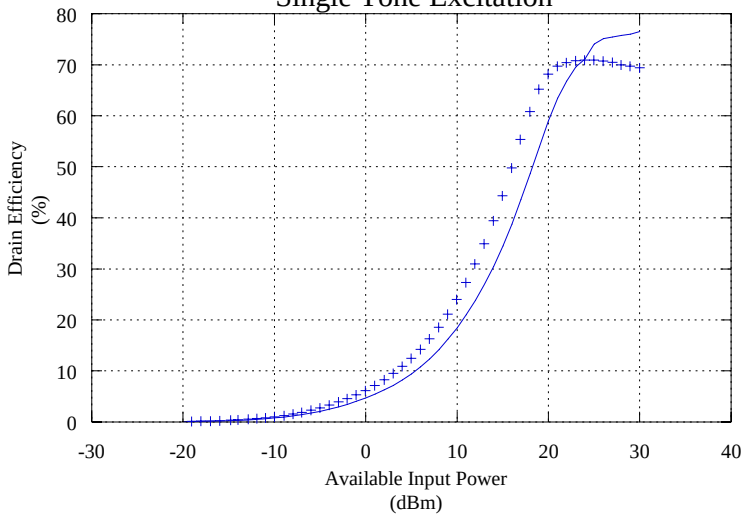
Transducer Gain vs. Available Input Power
Single Tone Excitation



Power Gain vs. Available Input Power
Single Tone Excitation



Drain Efficiency vs. Available Input Power
Single Tone Excitation

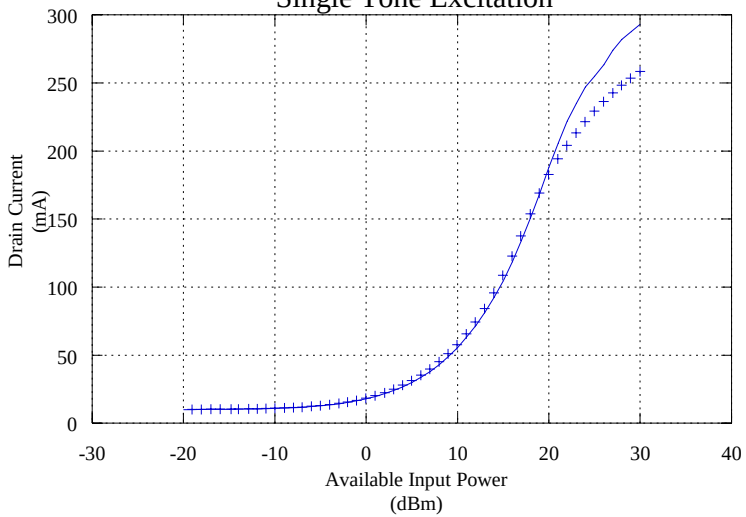


Rev/Date: Rev0/0298

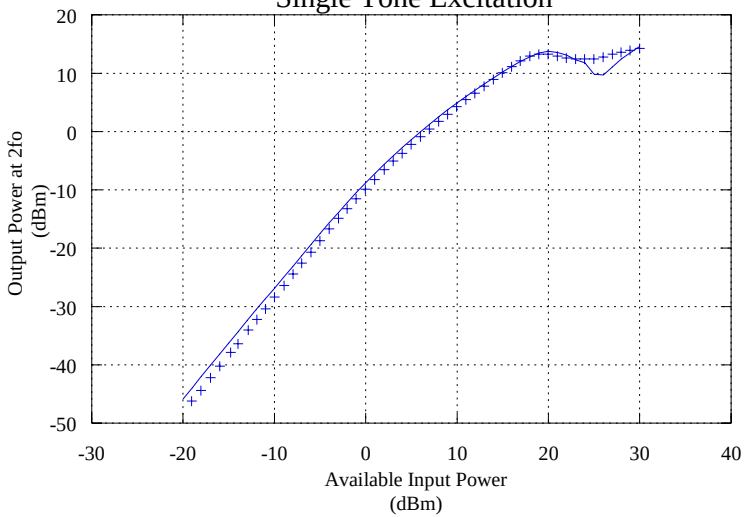
Simulated:hv3ped03swp1.txt & Measured:hv3ped03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power & Efficiency
Solid:Simulated & Points:Measured

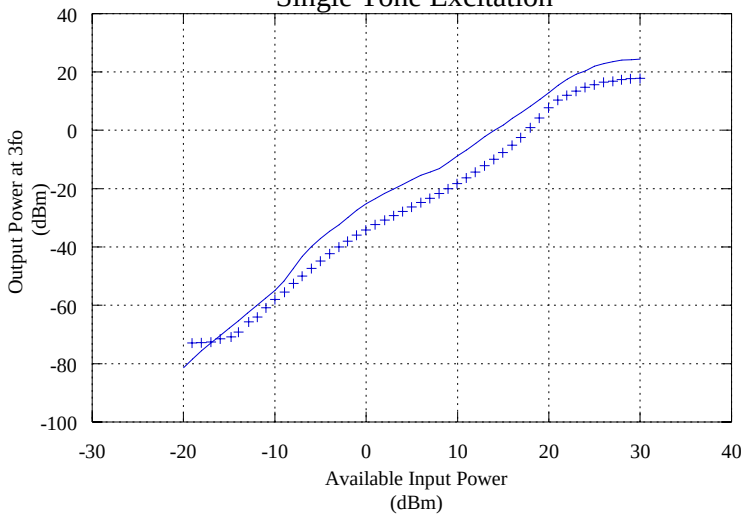
Drain Current vs. Available Input Power
Single Tone Excitation



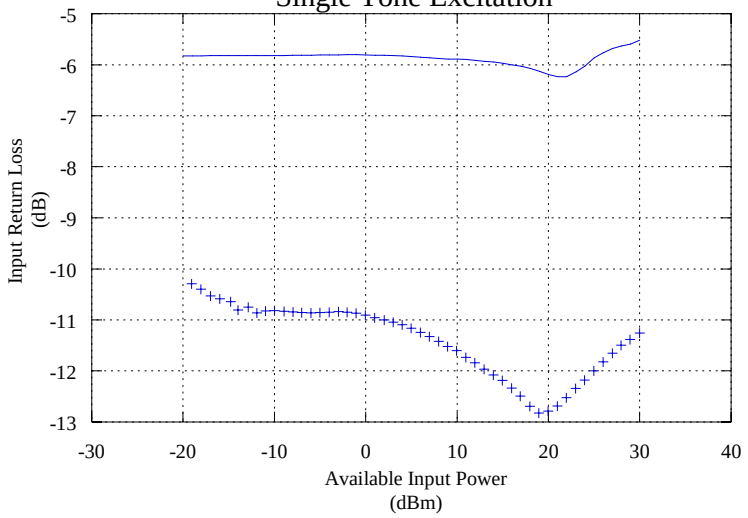
Output Power at 2fo vs. Available Input Power
Single Tone Excitation



Output Power at 3fo vs. Available Input Power
Single Tone Excitation



Input Return Loss vs. Available Input Power
Single Tone Excitation



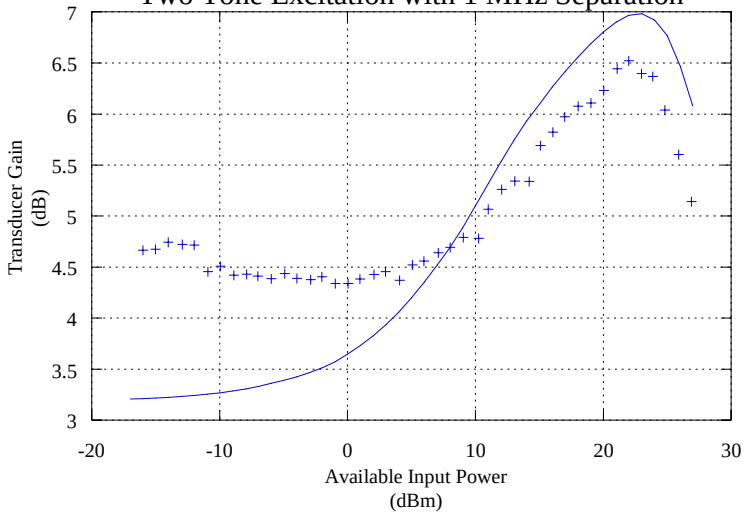
Rev/Date: Rev0/0298

Simulated:hv3ped03swp1.txt & Measured:hv3ped03.swp

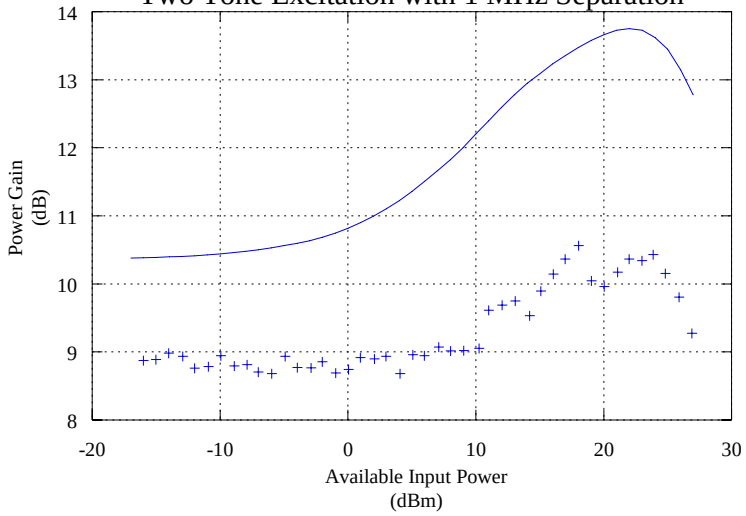
1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
50 ohm Termination
Solid:Simulated & Points:Measured

Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

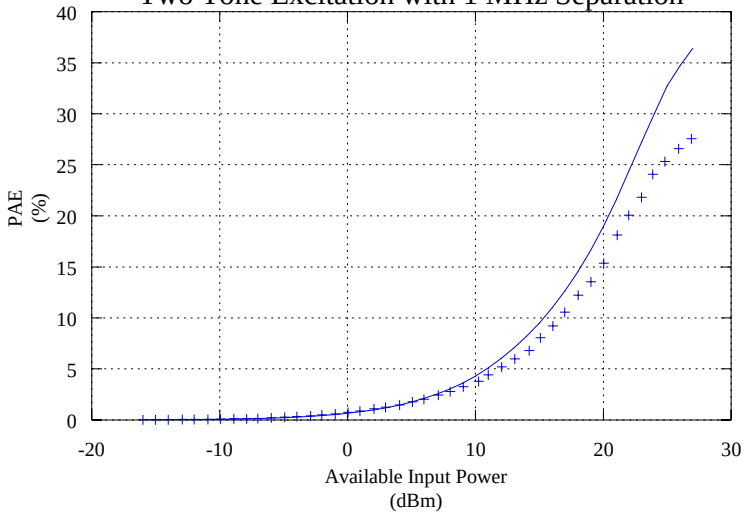
Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

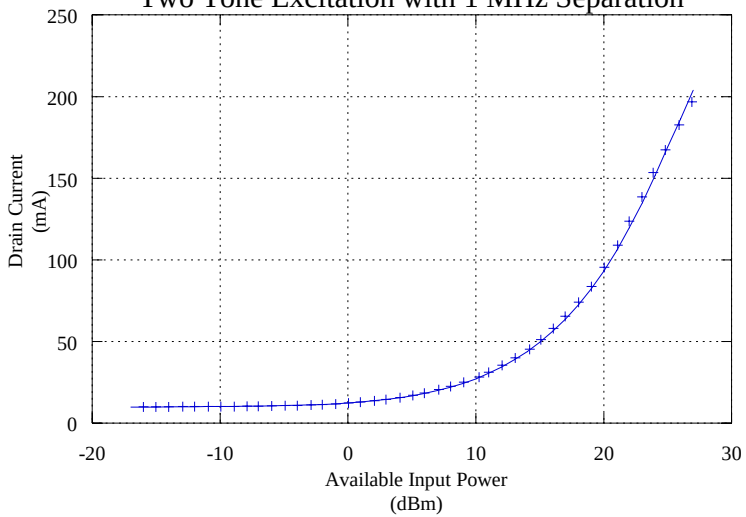


Rev/Date: Rev0/0298

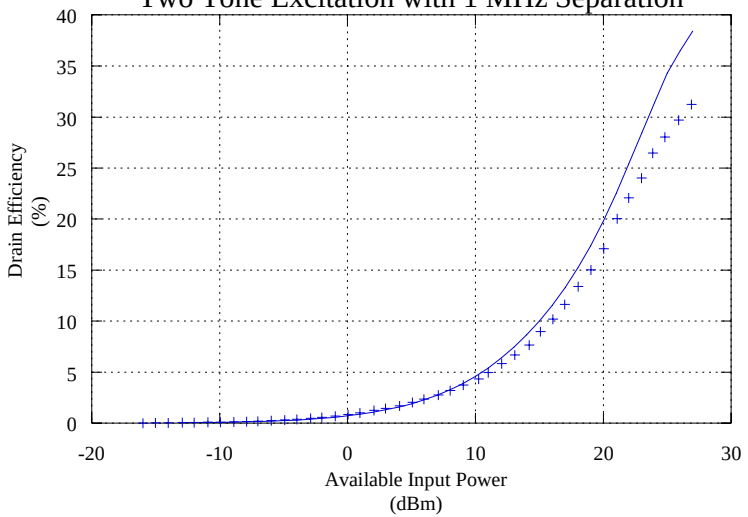
Simulated:hv3i5d03swp1.txt & Measured:hv3i5d03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
50 ohm Termination
Solid:Simulated & Points:Measured

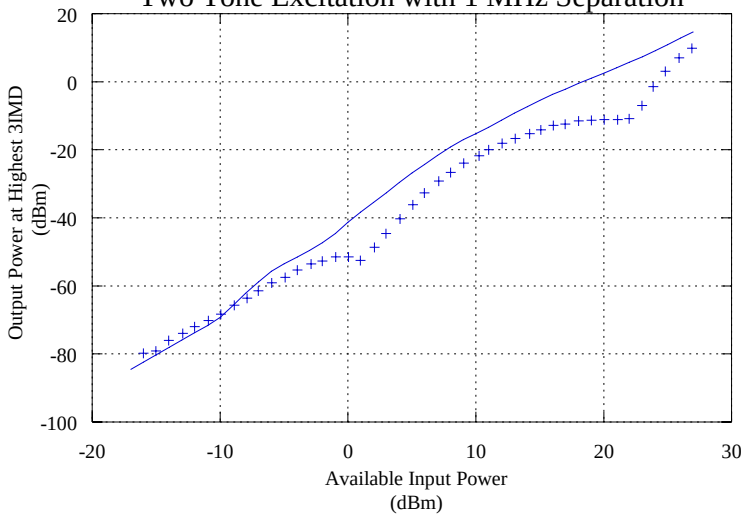
Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



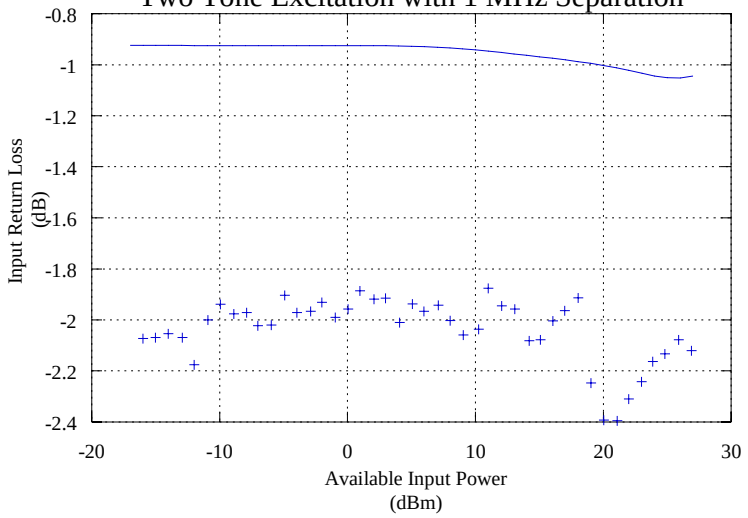
Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Output Power at HIghest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

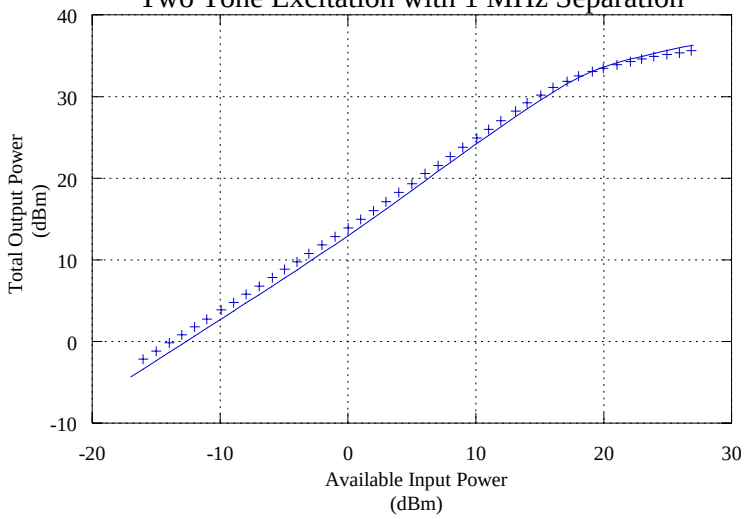


Rev/Date: Rev0/0298

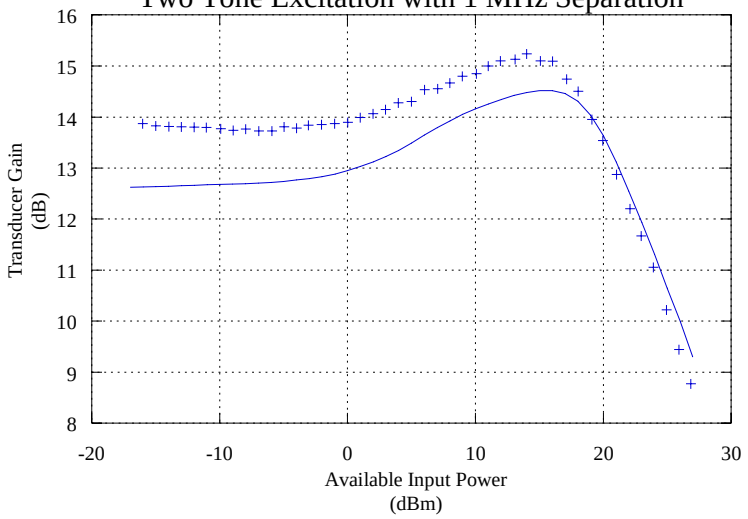
Simulated:hv3i5d03swp1.txt & Measured:hv3i5d03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power
Solid:Simulated & Points:Measured

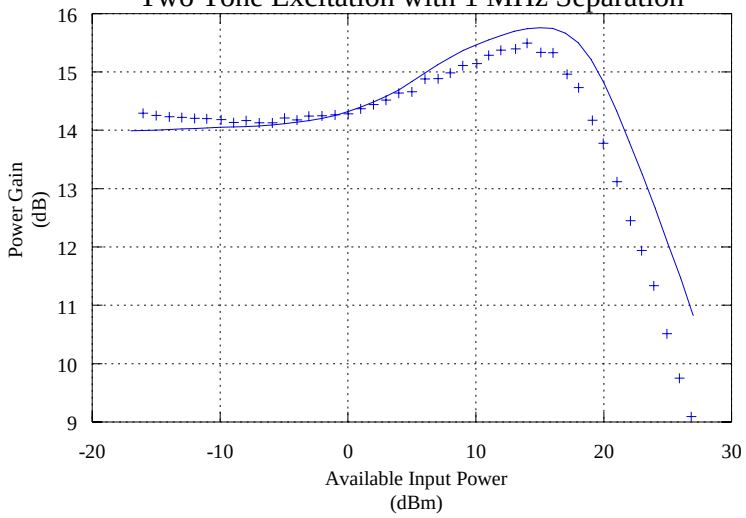
Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



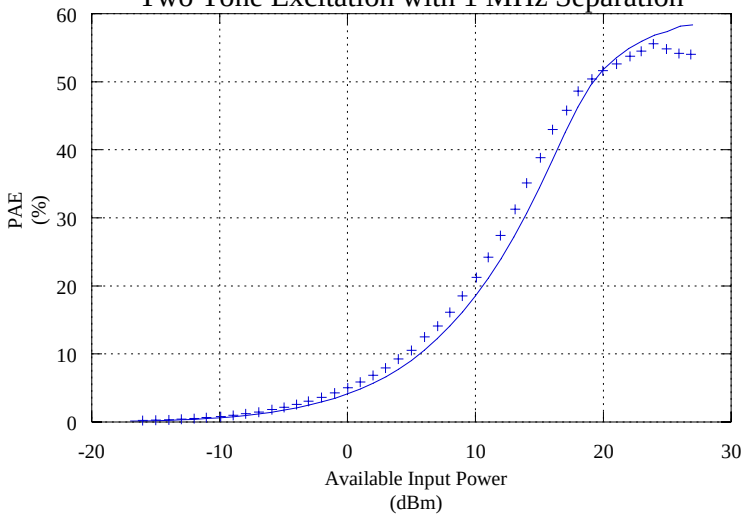
Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

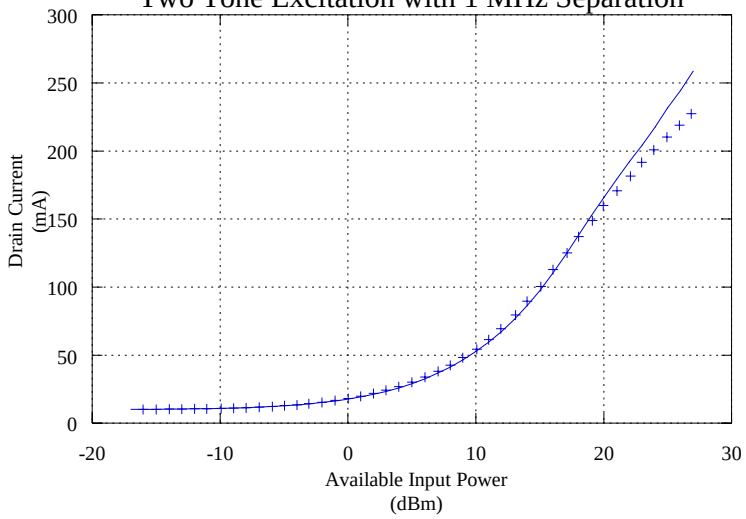


Simulated:hv3ipd03swp1.txt & Measured:hv3ipd03.swp

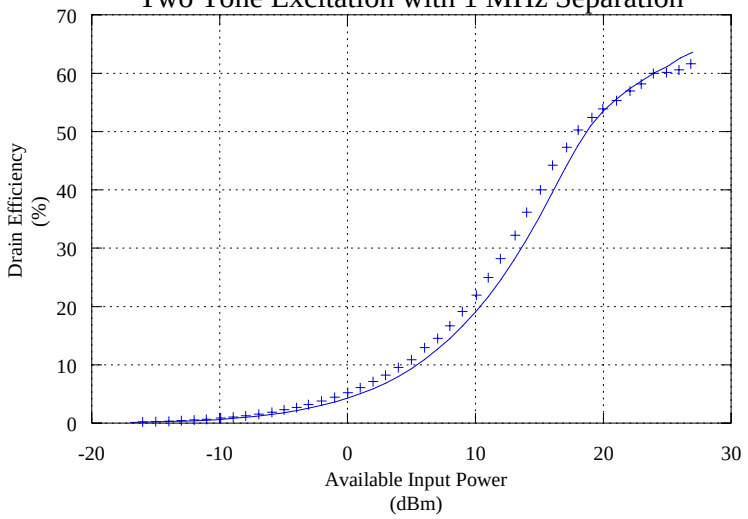
Rev/Date: Rev0/0298

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power
Solid:Simulated & Points:Measured

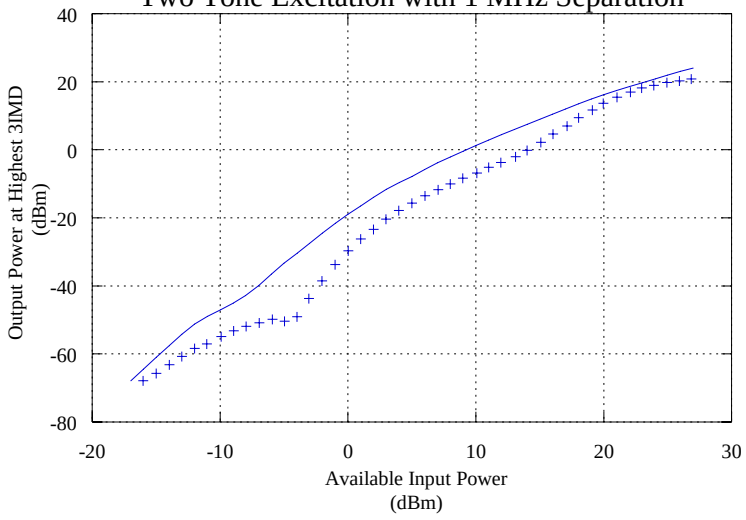
Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Output Power at HIghest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Simulated:hv3ipd03swp1.txt & Measured:hv3ipd03.swp

Rev/Date: Rev0/0298

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Efficiency
Solid:Simulated & Points:Measured

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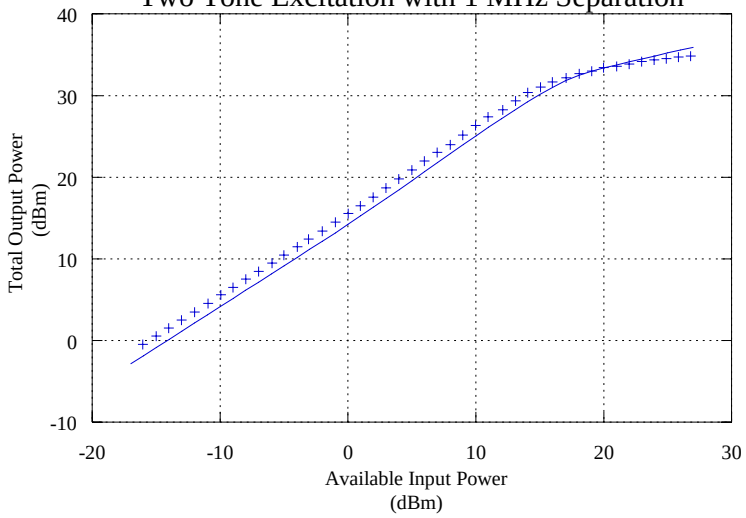
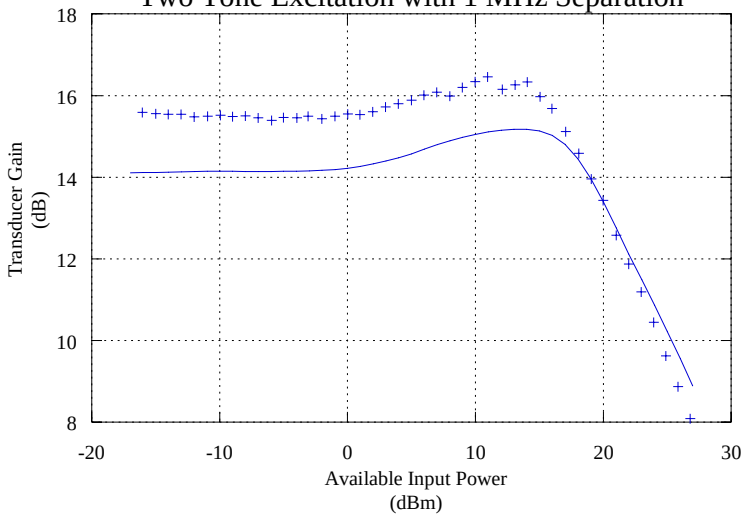
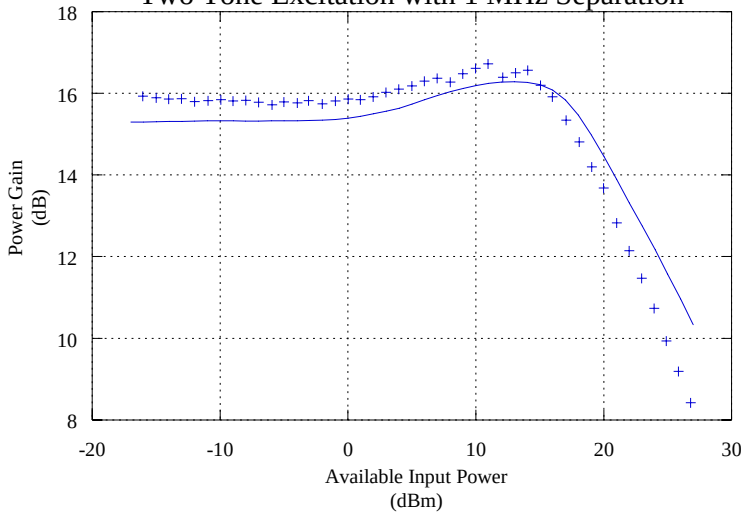
Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



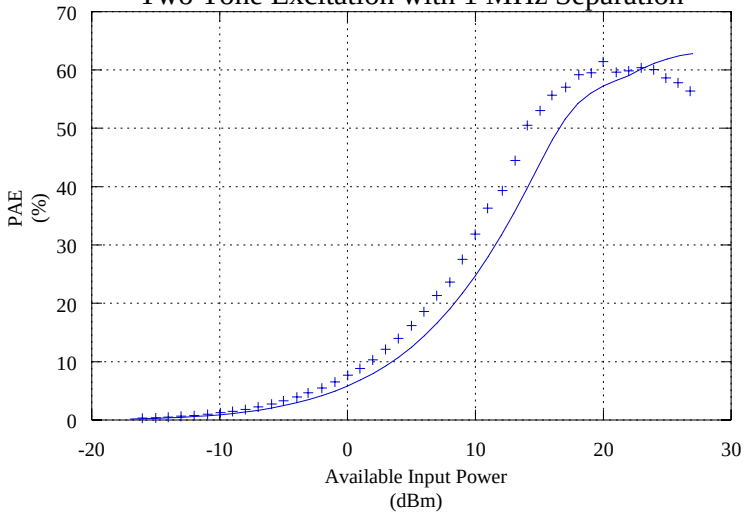
Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Rev/Date: Rev0/0298

Simulated:hv3ied03swp1.txt & Measured:hv3ied03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Efficiency
Solid:Simulated & Points:Measured

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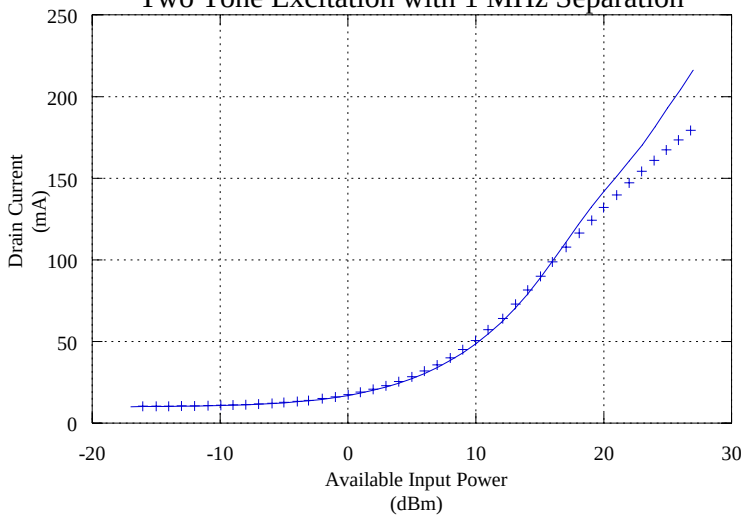
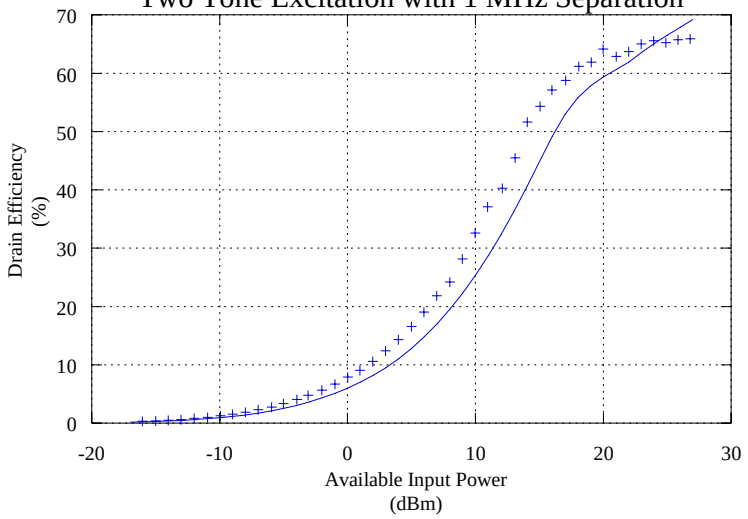
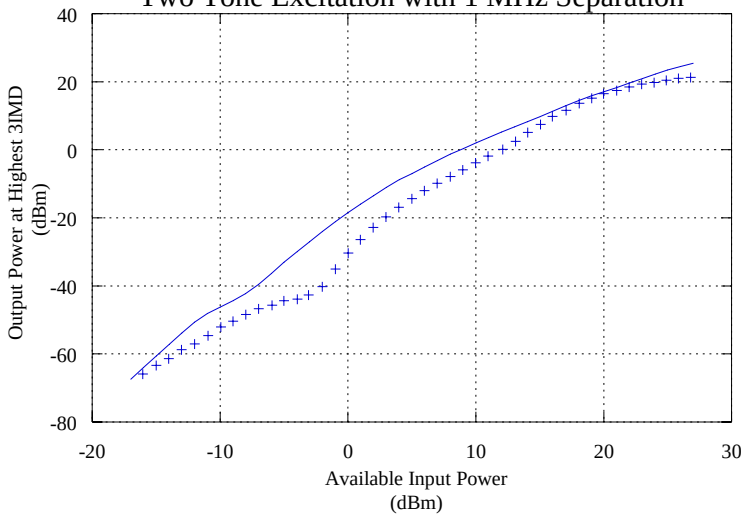
Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



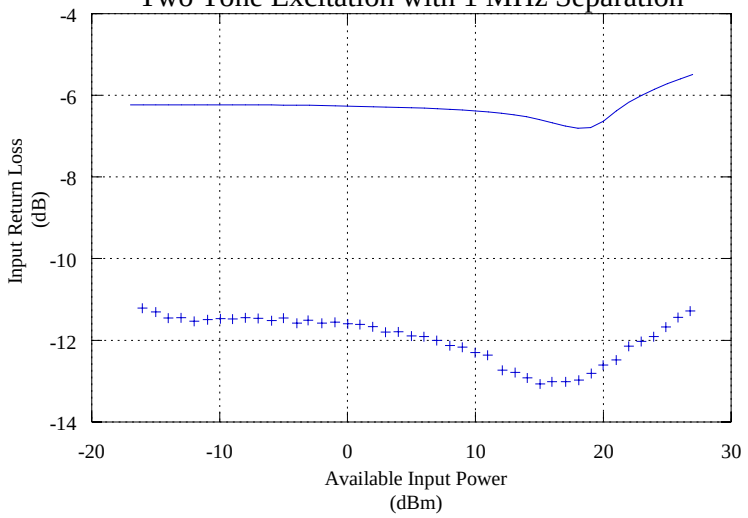
Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Output Power at HIghest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Rev/Date: Rev0/0298

Simulated:hv3ied03swp1.txt & Measured:hv3ied03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power & Efficiency
Solid:Simulated & Points:Measured

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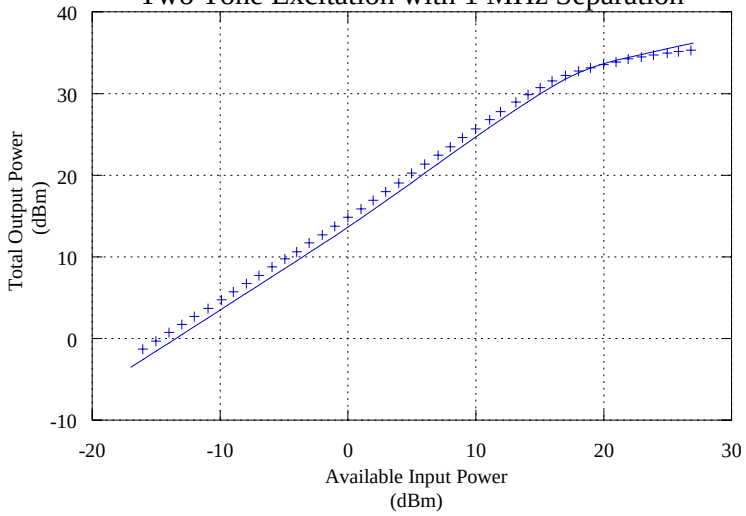
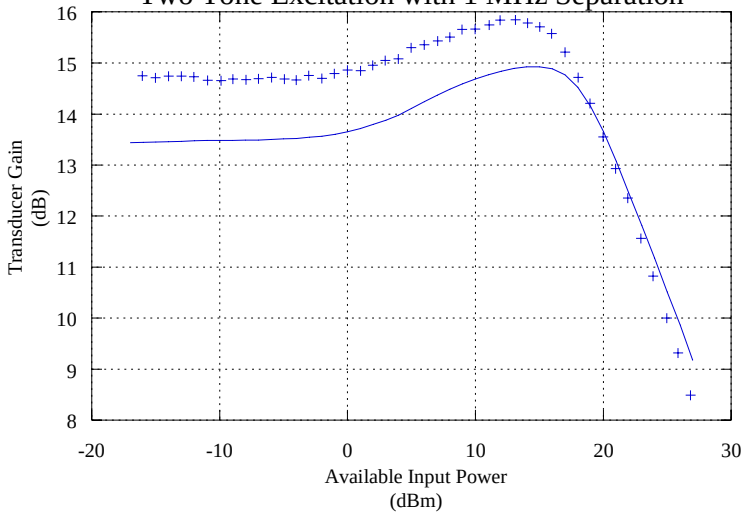
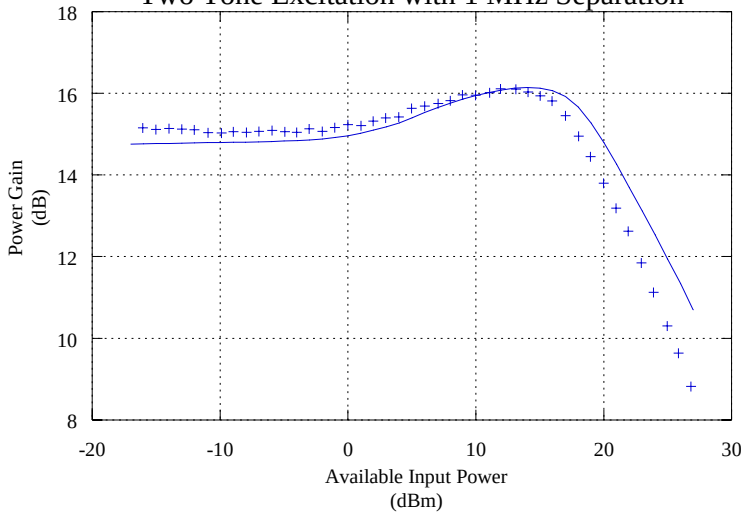
Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



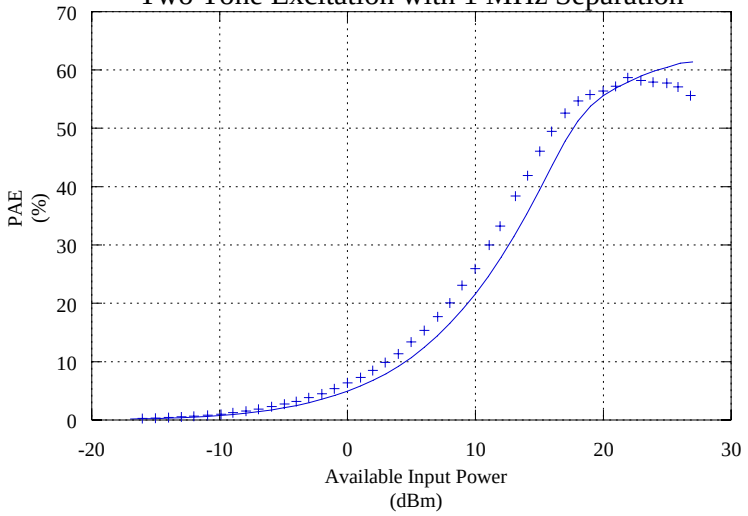
Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

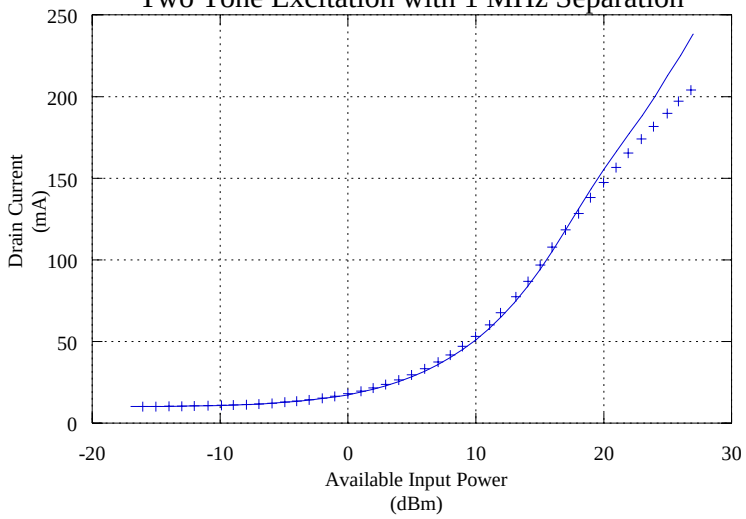


Rev/Date: Rev0/0298

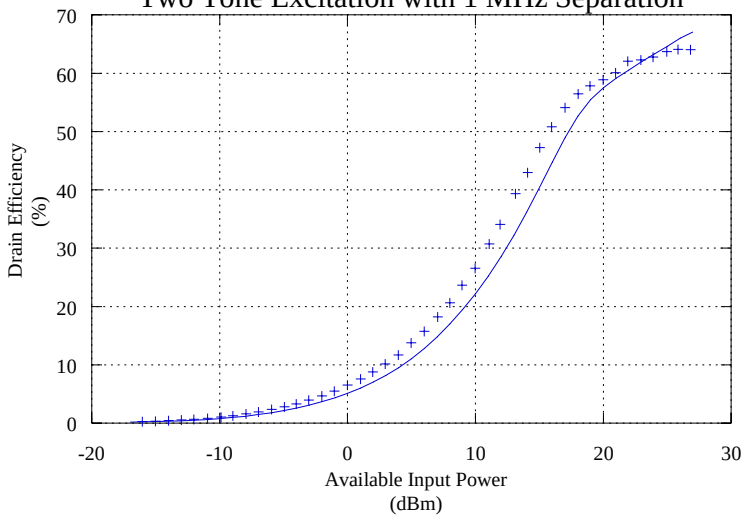
Simulated:hv3icd03swp1.txt & Measured:hv3icd03.swp

1 Block HV3 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 2 GHz, V_{DS}=26 v & I_{DS}=2.0 mA/mm
Tuned for Power & Efficiency
Solid:Simulated & Points:Measured

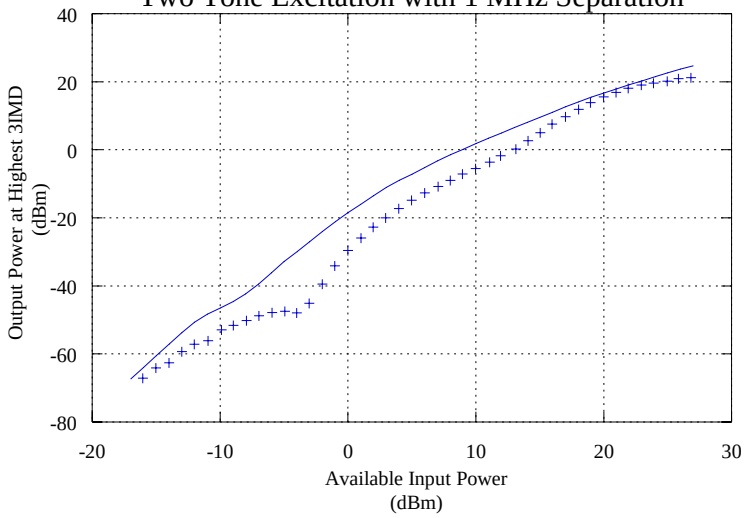
Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



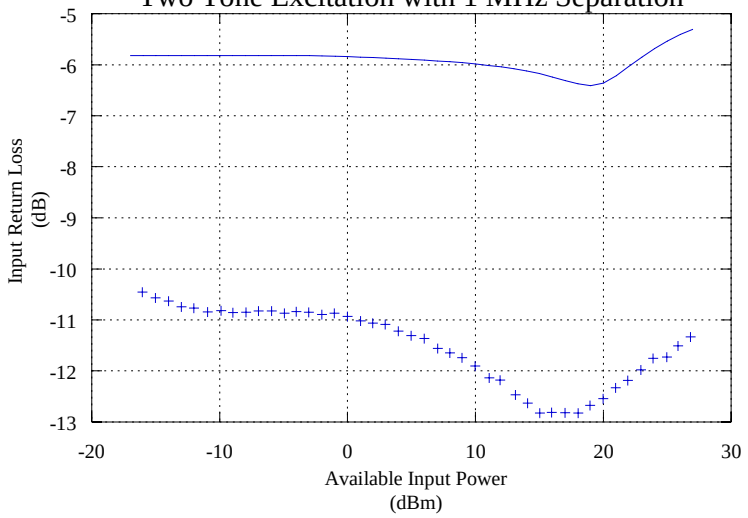
Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Output Power at HIghest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Simulated:hv3icd03swp1.txt & Measured:hv3icd03.swp

Rev/Date: Rev0/0298

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